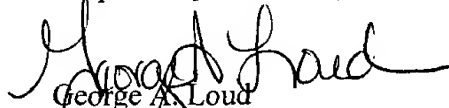


Please add the following new claims:

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- 13. A semiconductor device manufacturing method according to claim 7, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.
14. A semiconductor device manufacturing method according to claim 8, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.
15. A semiconductor device manufacturing method according to claim 11, wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.--

Respectfully submitted,


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12. (Amended) A semiconductor device manufacturing method according to claim 6 [any one of claims 6, 7, 8, and 11], wherein the insulating film is a silicon-containing insulating film which is formed by a thermal chemical vapor deposition employing a reaction gas that contains an ozone-containing gas and a tetraethylorthosilicate.

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